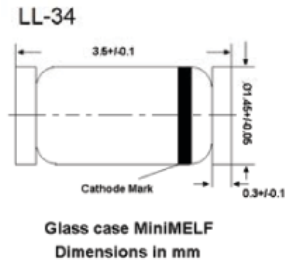


Silicon Epitaxial Planar Switching Diode

for general purpose and switching.



Maximum Ratings and Electrical Characteristics

Type	Peak Reverse Voltage	Aver. Rectified Current	Power Dissip. at 25 °C	Junction Temperature	Forward Voltage		Reverse Current		Reverse Recovery Time	
	V_{RM}	$I_{F(AV)}$	P_{tot}	T_J	V_F	at I_F	I_R	at V_R	t_{rr}	Conditions
	(V)	Max.(mA)	(mW)	(°C)	Max.(V)	(mA)	Max.(nA)	(V)	Max.(ns)	
LL914	100	75	500	200	1	10	25	20	4	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4149	100	150	500	200	1	10	25	20	4	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4152	40	150	400	175	0.55	0.1	50	30	2	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4154	35	150	500	200	1	30	100	25	2	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4447	100	150	500	200	1	20	25	20	4	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4449	100	150	500	200	1	30	25	20	4	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4450	40	150	400	175	0.54	0.5	50	30	4	$I_F = I_R = 10 \text{ mA}$, to $I_R = 1 \text{ mA}$
LL4451	40	150	400	175	0.5	0.1	50	30	10	$I_F = I_R = 10 \text{ mA}$, to $I_R = 1 \text{ mA}$
LL4453	30	150	400	175	0.55	0.01	50	20	-	-
LL4454	75	150	400	175	1	10	100	50	4	$I_F = I_R = 10 \text{ mA}$, to $I_R = 1 \text{ mA}$